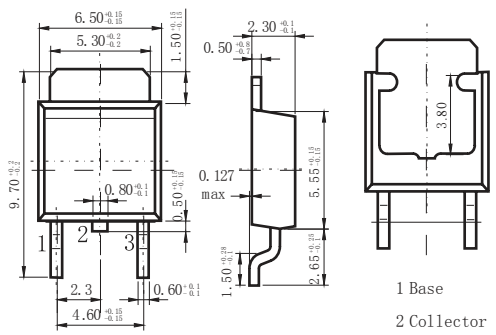
NPN Transistors

2SD1252

TO-252

Unit: mm



1 Base
2 Collector
3 Emitter

■ Features

- High forward current transfer ratio hFE which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Complementary to 2SB929

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	60	V
Collector - Emitter Voltage	V_{CEO}	60	
Emitter - Base Voltage	V_{EBO}	6	
Collector Current - Continuous	I_C	3	A
Collector Current - Pulse	I_{CP}	5	
Collector Power Dissipation Tc = 25℃	P_C	35	W
Ta = 25℃		1.3	
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 100 μA, I_E= 0	60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= 30 mA, I_B= 0	60			
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 μ A, I_C= 0	6			
Collector-base cut-off current	I_{CBO}	V_{CB}= 60 V , I_E= 0			0.1	mA
Collector cutoff current	I_{CES}	V_{CB}= 60 V , I_E= 0			200	uA
Collector cutoff current	I_{CEO}	V_{CB}= 30 V , I_E= 0			300	
Emitter cut-off current	I_{EBO}	V_{EB}= 5V , I_C=0			0.1	mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=3 A, I_B=375mA			1.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=3 A, I_B=375mA			1.2	
Base - emitte voltage	V_{BE}	V_{CE}= 4V, I_C= 3 A			1.8	
DC current gain	$h_{FE(1)}$	V_{CE}= 4V, I_C= 1A	40		250	
	$h_{FE(2)}$	V_{CE}= 4V, I_C= 3A	10			
Turn-on time	t_{on}	I_C = 1A, I_{B1} = 0.1A, I_{B2} = – 0.1A, V_{CC} = 50V		0.5		us
Storage time	t_{stg}			2.5		
Fall time	t_f			0.4		
Transition frequency	f_T	V_{CE}= 5V, I_C= 500mA,f=10MHz		30		MHz

■ Classification of $h_{fe(1)}$

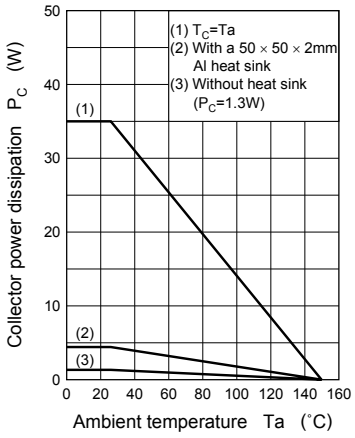
Type	2SD1252-R	2SD1252-Q	2SD1252-P
Marking	40-90	70-150	120-250

NPN Transistors

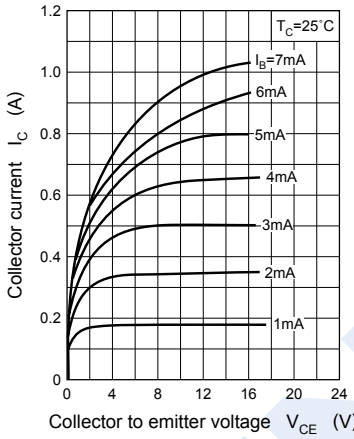
2SD1252

■ Typical Characterisitics

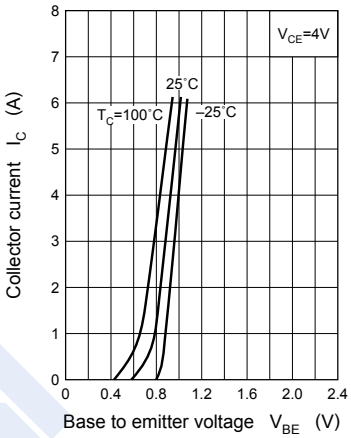
P_C — Ta



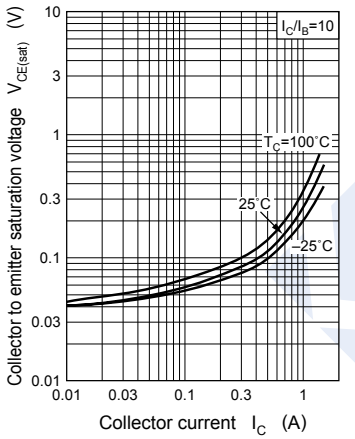
I_C — V_{CE}



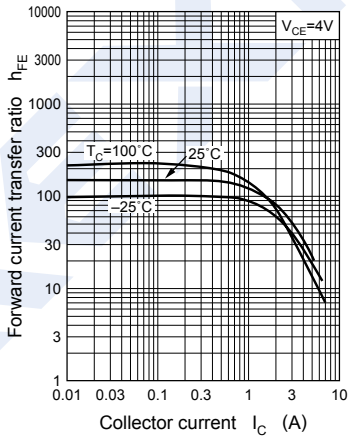
I_C — V_{BE}



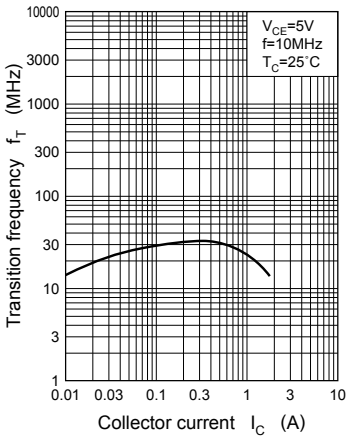
$V_{CE(sat)}$ — I_C



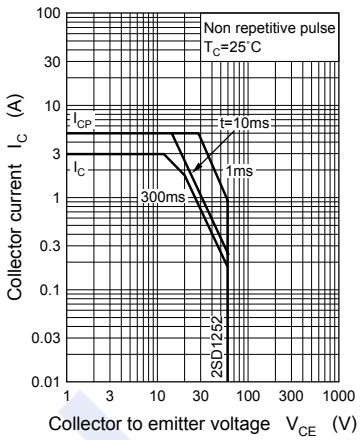
h_{FE} — I_C



f_T — I_C



Area of safe operation (ASO)



$R_{th(t)}$ — t